



40V PNP SMALL SIGNAL TRANSISTOR IN DFN0806

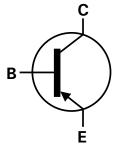
Features

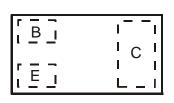
- BV_{CEO} > -40V
- I_C = -200mA high Collector Current
- P_D = 435mW Power Dissipation
- 0.48mm² package footprint, 16 times smaller than SOT23
- 0.4mm height package minimizing off-board profile
- Complementary NPN Type MMBT3904FA
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208
- Weight: 0.0008 grams (approximate)







Device Symbol

Top View Device Schematic

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906FA-7B	3N	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View Bar Denotes Base and Emitter Side

3N = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Continuous Collector Current	Ic	-200	mA
Peak Pulse Collector Current	I _{CM}	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ hetaJL}$	150	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

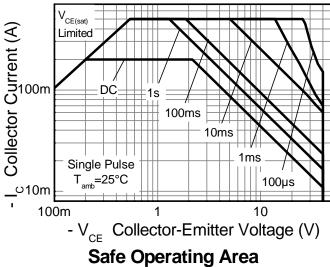
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

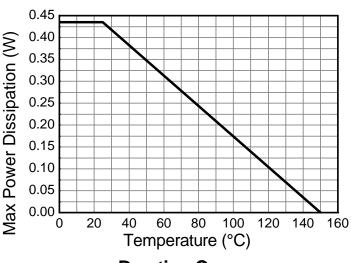
Notes:

For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



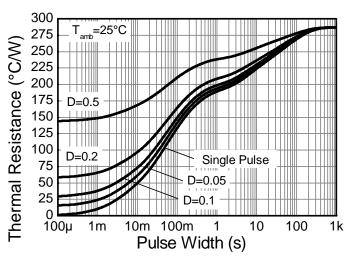
Thermal Characteristics and Derating Information

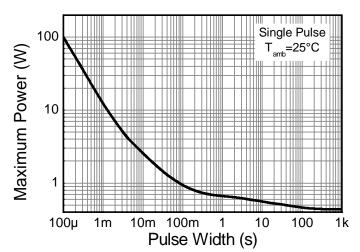












Transient Thermal Impedance

Pulse Power Dissipation



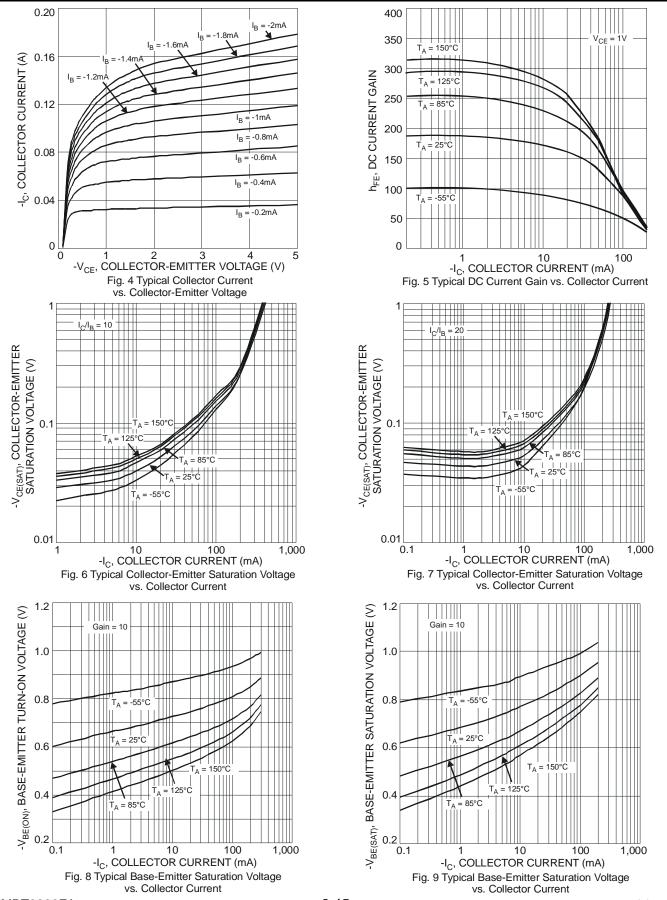
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-40	_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-6.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Collector Cutoff Current	I _{CBO}		-50	nA	$V_{CB} = -30V, I_{E} = 0$
Base Cutoff Current	I _{BL}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h _{FE}	60 80 100 60 30	300 — —	_	$\begin{split} I_C &= -100 \mu A, \ V_{CE} = -1.0 V \\ I_C &= -1.0 m A, \ V_{CE} = -1.0 V \\ I_C &= -10 m A, \ V_{CE} = -1.0 V \\ I_C &= -50 m A, \ V_{CE} = -1.0 V \\ I_C &= -100 m A, \ V_{CE} = -1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25 -0.40	V	$I_C = -10$ mA, $I_B = -1.0$ mA $I_C = -50$ mA, $I_B = -5.0$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65 —	-0.85 -0.95	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$ $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}		4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}		10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	2.0	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = -10V, I_{C} = -1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f _T	300	_	MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t _r	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t _f	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

Note: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



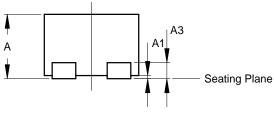
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

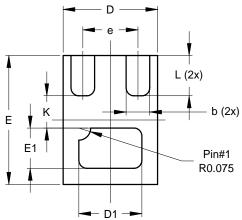




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

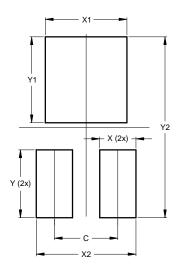




X2-DFN0806-3				
Dim	Min	Max	Тур	
Α	0.375	0.40	0.39	
A1	0	0.05	0.02	
А3	-	-	0.10	
b	0.10	0.20	0.15	
D	0.55	0.65	0.60	
D1	0.35	0.45	0.40	
Е	0.75	0.85	0.80	
E1	0.20	0.30	0.25	
е	-	-	0.35	
K	-	-	0.20	
٦	0.20	0.30	0.25	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value			
Dillielisions	(in mm)			
С	0.350			
Х	0.200			
X1	0.450			
X2	0.550			
Y	0.375			
Y1	0.475			
Y2	1.000			

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